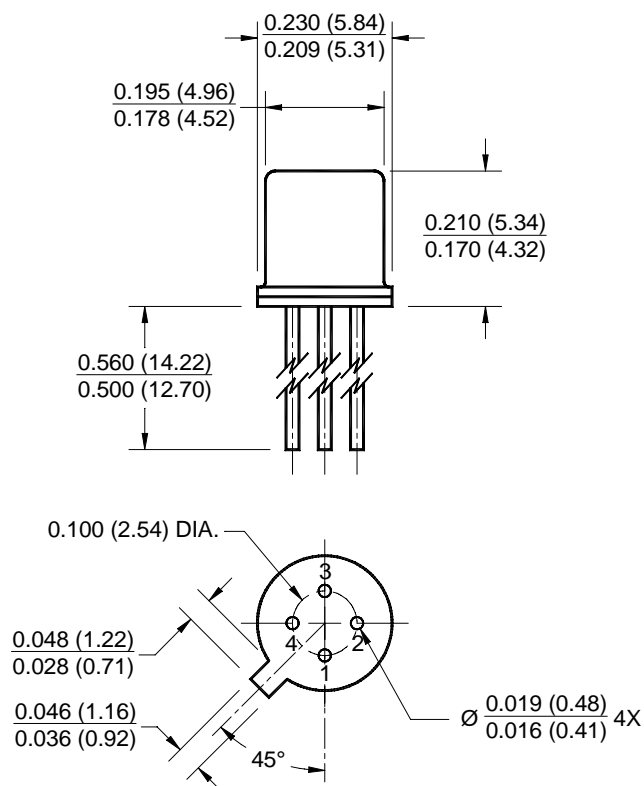
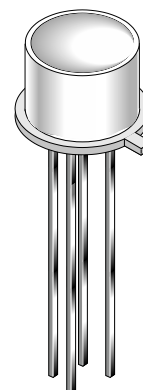


PACKAGE DIMENSIONS

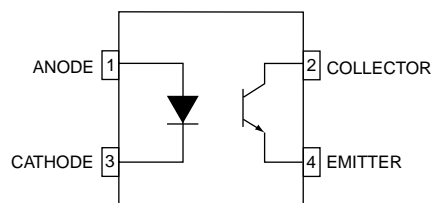


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The MCT4 is a standard four-lead, TO-18 package containing a GaAs infrared emitting diode optically coupled to an NPN silicon planar phototransistor.

FEATURES

- Hermetically package
- High current transfer ratio; typically 35%
- High isolation resistance; 10^{11} ohms at 500 volts
- High voltage isolation emitter to detector

MCT4

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Rating | Unit |
|--|-------------|----------------|------------------|
| Operating Temperature | T_{OPR} | -55 to +125 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | -65 to +150 | $^\circ\text{C}$ |
| Soldering Temperature (Flow) | T_{SOL-F} | 260 for 10 sec | $^\circ\text{C}$ |
| EMITTER | | | |
| Power Dissipation at 25°C Ambient ⁽¹⁾ | P_D | 90 | mW |
| Continuous Forward Current | I_F | 40 | mA |
| Reverse Voltage | V_R | 3 | V |
| Forward Current - Peak (1 μs pulse, 300 pps) | $I_{F(pk)}$ | 3.0 | A |
| DETECTOR | | | |
| Power Dissipation 25°C Ambient ⁽²⁾ | P_D | 200 | mW |
| Collector to Emitter Voltage | V_{CEO} | 30 | V |
| Emitter to Collector Voltage | V_{ECO} | 7 | V |
| COUPLER | | | |
| Total Power Dissipation ⁽³⁾ | P_D | 250 | mW |
| Isolation Voltage | | 1000 | VDC |

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

INDIVIDUAL COMPONENT CHARACTERISTICS

| Parameters | Test Conditions | Symbol | Min | Typ | Max | Units |
|---|---|------------|-----|------|------|---------------|
| EMITTER | | | | | | |
| Forward Voltage | $I_F = 40\text{ mA}$ | V_F | | 1.30 | 1.50 | V |
| Reverse Current | $V_R = 3.0\text{ V}$ | I_R | | 0.15 | 10 | μA |
| Capacitance | $V = 0\text{ V}$ | C | | 150 | | pF |
| DETECTOR | | | | | | |
| Breakdown Voltage Collector to Emitter | $I_C = 1.0\text{ mA}, I_F = 0$ | BV_{CEO} | 30 | | | V |
| Emitter to Collector | $I_E = 100\text{ }\mu\text{A}, I_F = 0$ | BV_{ECO} | 7 | 12 | | V |
| Leakage Current Collector to Emitter | $V_{CE} = 10\text{ V}, I_F = 0$ | I_{CEO} | | 5 | 50 | nA |
| Capacitance Collector to Emitter | $V_{CE} = 0$ | C_{CE} | | 2 | | pF |

NOTE:

- Derate power linearly 1.2 mW/ $^\circ\text{C}$ above 25°C
- Derate power linearly 2.67 mW/ $^\circ\text{C}$ above 25°C
- Derate power linearly 3.3 mW/ $^\circ\text{C}$ above 25°C

MCT4

| TRANSFER CHARACTERISTICS (T _A = 25°C Unless otherwise specified.) | | | | | | |
|--|---|----------------------|-----|-----|-----|-------|
| DC Characteristics | Test Conditions | Symbol | Min | Typ | Max | Units |
| COUPLED | | | | | | |
| DC current Transfer Ratio (note 1) | V _{CE} = 10 V, I _F = 10 mA | CTR | 15 | 35 | | % |
| Saturation Voltage | I _C = 500 μA, I _F = 10 mA | V _{CE(SAT)} | | 0.1 | | V |
| | I _C = 2 mA, I _F = 50 mA | | | 0.2 | 0.5 | |
| AC Characteristics | Test Conditions | Symbol | Min | Typ | Max | Units |
| Capacitance LED to Detector | | | | 1.8 | | pF |
| Bandwidth (Fig. 5) | Note 2 | | | 300 | | kHz |
| Rise Time and Fall Time (see operating schematic) | I _C = 2 mA, V _{CE} = 10 V, Note 3 | | | 2 | | μs |

| ISOLATION CHARACTERISTICS | | | | | | |
|---------------------------|-----------------|------------------|------------------|------------------|-----|-------|
| Characteristic | Test Conditions | Symbol | Min | Typ | Max | Units |
| Isolation Resistance | V = 500 VDC | R _{ISO} | 10 ¹¹ | 10 ¹² | | Ω |
| Breakdown Voltage | Time = 1 sec | | 1000 | 1500 | | VDC |

NOTE:

1. The current transfer ratio (I_C/I_F) is the ratio of the detector collector current to the LED input current with V_{CE} at 10 volts.
2. The frequency at which i_c is 3 dB down from the 1 kHz value.
3. Rise time (t_r) is the time required for the collector current to increase from 10% of its final value, to 90%. Fall time (t_f) is the time required for the collector current to decrease from 90% of its initial value to 10%.

Figure 1. Detector Output Characteristics

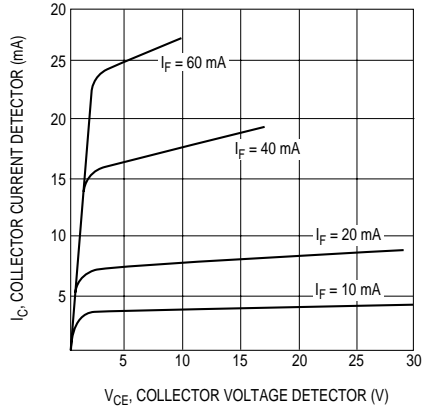


Figure 2. Input Current vs. Output Current

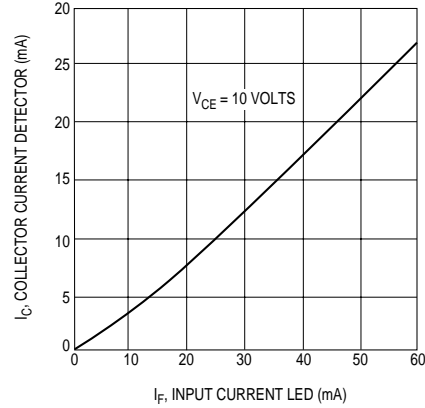


Figure 3. Dark Current vs. Temperature

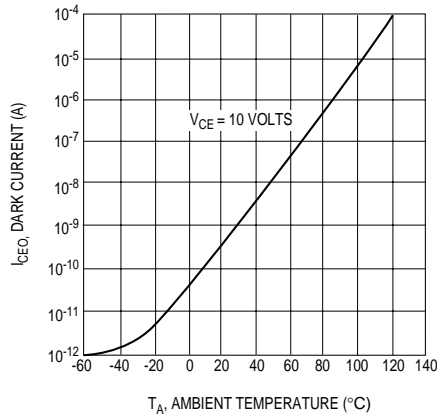


Figure 4. Current Output vs. Temperature

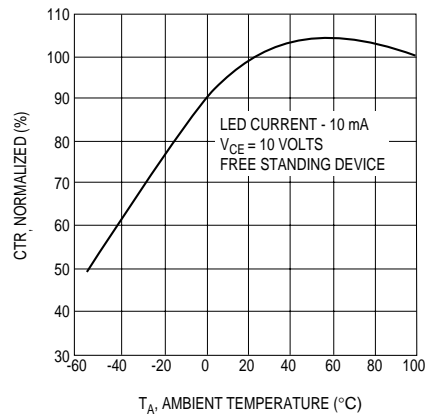


Figure 5. Output vs. Frequency

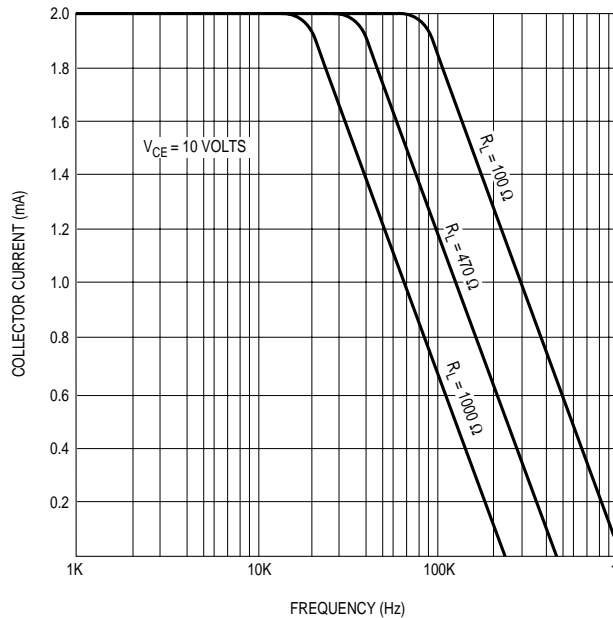
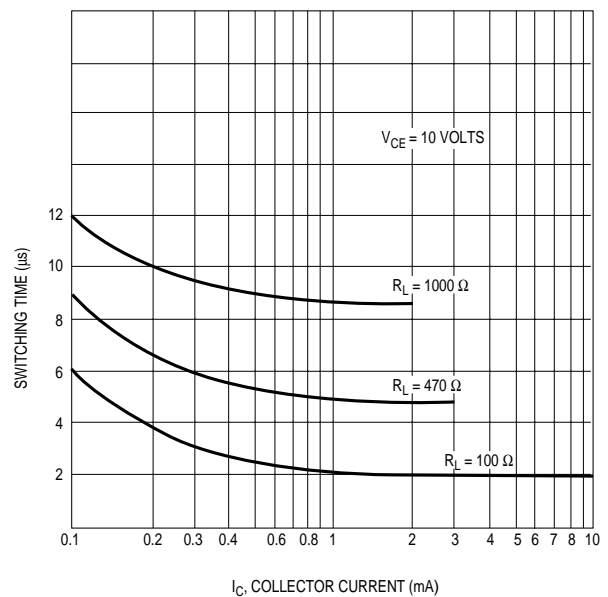


Figure 6. Switching Time vs. Collector Current



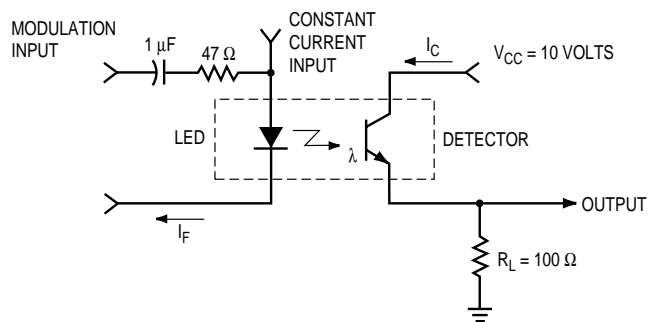


Figure 7. Modulation Circuit Used to Obtain Output vs. Frequency Plot

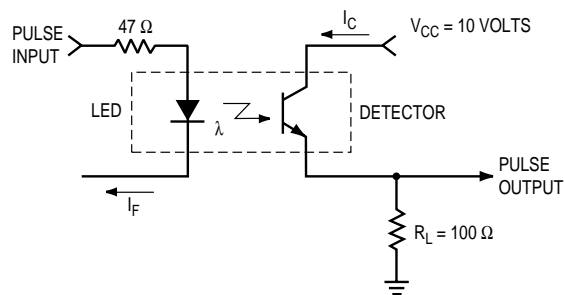


Figure 8. Circuit Used to Obtain Switching Time vs. Collector Current Plot

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